

2N3773/2N6099

COMPLEMENTARY SILICON TRANSISTORS

DESCRIPTION

The UTC **2N3773/2N6099** are complement silicon power transistors designed for high power audio, disk head positions and other linear applications. These device can be used in power switching circuits such as relay or solenoid drivers, DC to DC converters or inverts.

FEATURES

- * Complement Characterized for linear operation
- * High DC Current Gain and low saturation voltage h_{EE}>15(8A, 4V)
- V_{CE(SAT)}<1.4V(I_C=8A, I_B=0.8A)
- * For Low Distortion Complementary Designs

ORDERING INFORMATION

Ordering Number		Dealers	Pin Assignment			De elvie e	
Lead Free	Halogen Free	Раскаде	1	2	3	Раскілд	
2N3773L-T30-Y	2N3773G-T30-Y	TO-3	В	E	С	Tray	
2N6099L-T30-Y	2N6099G-T30-Y	TO-3	В	E	С	Tray	

2N3773L-T30-Y (1)Packing Type (2)Package Type (3)Lead Free	(1) Y: Tray (2) T30: TO-3 (3) G: Halogen Free, L: Lead Free
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POWER TRANSISTOR



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		Vcro	160	V
Collector-Emitter Volta	ade	VCEO	140	V
Emitter-Base Voltage		V _{EBO}	7	V
Collector-Emitter Voltage		V _{CEX}	160	V
Power Dissipation	T _C =25℃	5	150	W
	Dertate Above 25℃		0.855	W/°C
Collector Current	Continuous		16	А
	Peak	IC	30	А
Base Current	Continuous		4	А
	Peak	IB	15	А
Junction Temperature		TJ	150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse Test: Pw<=5ms, Duty Cycle<=10%

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ」c	1.17	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV_{CBO}	I _C =0.2A, I _B =0	160			V	
Collector-Emitter Sustaining Voltage	BV _{CEX}	$I_{C}=0.1A, V_{BE(OFF)}=1.5V, R_{BE}=100\Omega$	160			V	
Collector-Emitter Sustaining Voltage	BV_{CER}	I _C =0.1A, R _{BE} =100Ω	150			V	
Collector Cut-off Current	I _{CBO}	V _{CB} =140V, I _E =0			2	mA	
Emitter Cut-off Current	I _{EBO}	V _{BE} =7V, I _C =0			5	mA	
Collector Cut-off Current	I _{CEX}	V _{CE} =140V,V _{BE(OFF)} =1.5V		2		mA	
		V _{CE} =140V,V _{BE(OFF)} =1.5V,T _C =150°C		10		mA	
ON CHARACTERISTICS							
DC Current Gain (Note)	h _{FE1}	V _{CE} =4V, I _C =8A	15		60		
	h _{FE2}	V _{CE} =4V, I _C =16A	5				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =8A, I _B =800mA			1.4	V	
		I _C =16A, I _B =3.2A			4	V	
Base-Emitter Saturation Voltage	V _{BE(ON)}	I _C =8A, V _{CE} =4V			2.2	V	
DYNAMIC CHARACTERISTICS							
Small Signal Current Gain	h _{FE}	I _C =1A, V _{CE} =4V, f=1kHz	40				
Magnitade Of Commom-Emitter							
Small Signal, Short Circuit Forward	h _{FE}	I _C =1A, f=50kHz	4				
Current Transfer Ratio							
Second Breakdown Collector With	l₀/h	t=1s(non-repetive) Vor=100V	15			Δ	
Base Forward Biased	15/10	1 - 13(1101 - 10) = 1000	1.5			~	

Note: Pulse Test: Pw<=300µs, Duty Cycle<=2%



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